

Refine Search

1/11/748,828

Search Results -

Terms	Documents
L1 and ((protection or protecting) adj (film or layer))	2

Database:

US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L5

Search History

DATE: Wednesday, January 12, 2005 [Printable Copy](#) [Create Case](#)

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side by side

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result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L5</u>	L1 and ((protection or protecting) adj (film or layer))	2	<u>L5</u>
<u>L4</u>	L3 and ((protection or protecting) adj (film or layer))	0	<u>L4</u>
<u>L3</u>	L2 and gate	15	<u>L3</u>
<u>L2</u>	L1 and oxidation and anisotropic	15	<u>L2</u>
<u>L1</u>	polycide near9 ((titanium adj nitride) or TiN)	79	<u>L1</u>

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L5: Entry 2 of 2

File: USPT

Aug 19, 1997

DOCUMENT-IDENTIFIER: US 5659202 A

TITLE: Semiconductor device with a pair of dummy electrodes below an inner lead

Detailed Description Text (4):

A pair of dummy electrodes are respectively formed between each of the pads and the metal interconnection and between the metal interconnection and the edge of the semiconductor chip in the state of single-layer or double-layer, or multiple-layer structure. Pairs of dummy electrodes corresponding to the respective inner leads are preferably separated from each other as shown in FIG. 1. The configuration of the dummy electrodes is not particularly limited as long as the dummy electrodes are spaced apart a predetermined distance from the metal interconnection around the intersections of the inner leads and the dummy electrodes. Each of the dummy electrodes is preferably formed into a rectangular shape which extends generally parallel to the metal interconnection. Exemplary materials for the dummy electrodes include Al, AlSi, AlCu, AlSi/TiW, AlTi, TiN, polysilicon, silicides of polysilicon and high-melting-point metals, and polycides of such silicides and polysilicon. The thickness and width of the dummy electrodes are about 200 nm to about 1,000 nm and about 0.2 μm to about 10 μm , respectively.

Detailed Description Text (36):

Even if breakage of a protection film formed on a dummy electrode causes the inner lead to be short-circuited to the dummy electrode, the dummy electrode is only kept at the same potential as that applied to the pad, because the dummy electrode is electrically isolated from the other portions. Therefore, no erroneous operation occurs in the semiconductor device.

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Generate OACS				

Search Results - Record(s) 1 through 2 of 2 returned.

☐ 1. Document ID: US 6025256 A

L5: Entry 1 of 2

File: USPT

Feb 15, 2000

US-PAT-NO: 6025256

DOCUMENT-IDENTIFIER: US 6025256 A

TITLE: Laser based method and system for integrated circuit repair or reconfiguration

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	WAC	Draw D
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☐ 2. Document ID: US 5659202 A

L5: Entry 2 of 2

File: USPT

Aug 19, 1997

US-PAT-NO: 5659202

DOCUMENT-IDENTIFIER: US 5659202 A

TITLE: Semiconductor device with a pair of dummy electrodes below an inner lead

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	WAC	Draw D
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Terms	Documents
L1-and ((protection or protecting) adj (film or layer))	2

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